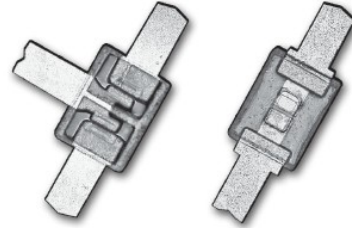


## Planar Beam Lead PIN Diode

Rev. V1

### Features

- Single / Common-Anode Configurations
- 4 Gram Minimum Lead Pull
- Oxide / Nitride / Polyimide Triple Passivation for High Reliability



### Description

The planar beam lead PIN diodes provide low microwave capacitance with exceptional lead strength. The high beam strength offers the users superior assembly yield. The oxide / nitride / polyimide passivation offers high reliability with low reverse leakage current and high temperature performance.

### Electrical Specifications<sup>1</sup>: $T_A = +25^\circ\text{C}$

Part #	Configuration	Reverse Current ( $I_R$ )	Breakdown Voltage ( $V_{BR}$ )	Junction Capacitance ( $C_J$ )	Series Resistance ( $R_S$ )	Lifetime (t)
		$V_R = 30\text{ V}$	$I_R = 10\ \mu\text{A}$	$V_R = 10\text{ V}, 15\text{ GHz}$	$I_F = 20\text{ mA}, 3\text{ GHz}$	
		nA	V	pF	$\Omega$	ns
		Max.	Min.	Max.	Max.	Typ.
MPND4005-B15 MPND4005-B16	Single Common Anode	100	100	0.02	6.5	125

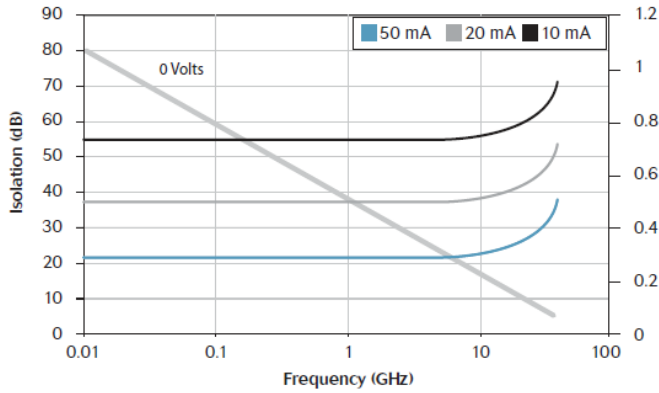
1. All devices available in a variety of packages. Consult factory for special version, high reliability screening or custom designs.

### Absolute Maximum Ratings

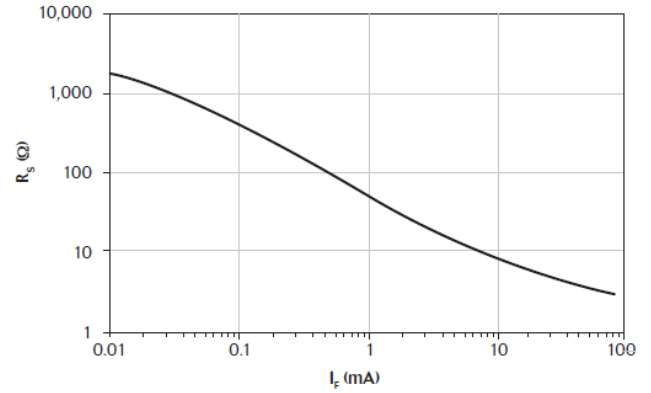
Parameter	Absolute Maximum
Total Power Dissipation	250 mW @ 25°C, Derate linearly to 0 @ +175°C
Operating Temperature	-65°C to +175°C
Storage Temperature	-65°C to +200°C
Terminal Strength	4 grams minimum

### Typical Performance Curves

Isolation vs. Frequency

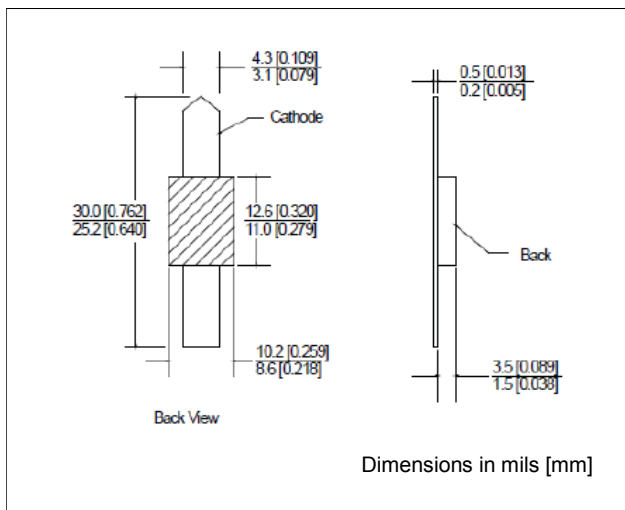


Forward Resistance vs. Current



### Outlines

#### B15



#### B16

